# 2SC5397

For High Frequency Amplify, Middle Frequency Amplify Silicon NPN Epitaxial Type Micro (Frame type)

#### **DESCRIPTION**

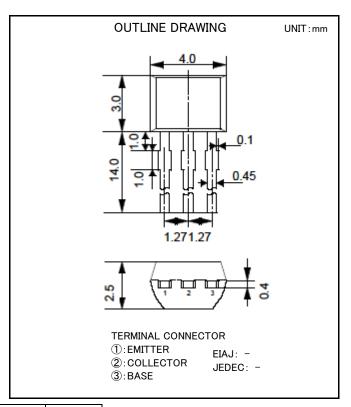
2SC5397 is a silicon NPN epitaxial type transistor.

## **FEATURE**

- · High gain 10.7MHz MAG=45dB typ
- · Low noise 10.7MHz NF=3.0dB typ
- · Low yre 10.7MHz yre -J0.11mS typ
- Small package

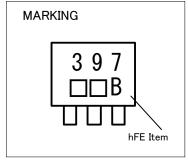
## APPLICATION

High frequency amplify, oscillating, frequency exchange, medium frequency amplify for small communication machine, FM/AM radio.



#### MAXIMUM RATINGS (Ta=25°C)

| Symbol           | Parameter  | Ratings | Unit |
|------------------|--|---------|------|
| Vcво             | Collector to Base voltage  | 30      | ٧    |
| V <sub>EBO</sub> | Vebo Emitter to Base voltage  Voeo Collector to Emitter voltage  Ic Collector current  Pc Collector dissipation  Tj Junction temperature  Tstg Storage temperature |         | V    |
| Vceo             |  |         | ٧    |
| Ic               |  |         | mA   |
| Pc               |  |         | mW   |
| Tj               |  |         | °C   |
| Tstg             |  |         | °C   |



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

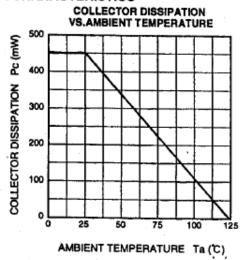
| Parameter    | Symbol                        |  | Limits |     |     |      |
|--------------|-------------------------------|--|--------|-----|-----|------|
|              |                               | Test conditions  |        | Тур | Max | Unit |
| ICBO         | Collector cut off current     | V $_{\text{CB}}$ = 30V , I $_{\text{E}}$ = 0mA                         | -      | -   | 1   | μΑ   |
| <b>I</b> EBO | Emitter cut off current       | $V_{EB}$ = 4V , I $_{C}$ = 0mA   | -      | -   | 1   | μΑ   |
| hFE          | DC forward current gain 💥     | $V_{CE} = 6V$ , $I_{C} = 1mA$  | 35     | -   | 300 | -    |
| fT           | Gain bandwidth product        | $V_{CE}$ = 6V , $I_{E}$ = -1mA   | 150    | 200 | -   | MHz  |
| Cob          | Collector output capacitance  | V $_{\text{CB}}$ = 6V , I $_{\text{E}}$ = 0mA,f=1MHz                   | -      | 2.0 | 2.7 | pF   |
| Ccrb'b       | Collector- base time constant | V <sub>CB</sub> =6V, I E=-1mA, f=31.8MHz                               | 1      | 20  | 60  | pS   |
| NF           | Noise figure                  | V $_{\text{CE}}$ = 6V , I $_{\text{E}}$ = -0.1mA,f=1kHz,RG=2k $\Omega$ |        | 3.0 | _   | dB   |

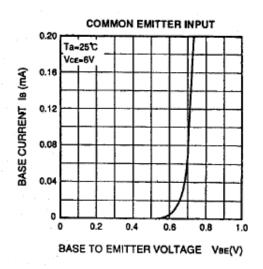
 $\divideontimes$  : It shows hFE classification at right table.

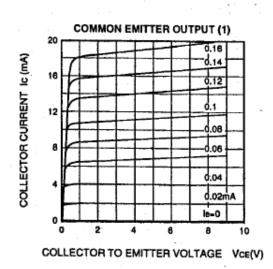
| Item | В              | С               | D      | E       |
|------|----------------|-----------------|--------|---------|
| hFE  | 35 <b>~</b> 70 | 55 <b>~</b> 110 | 90~180 | 150~300 |

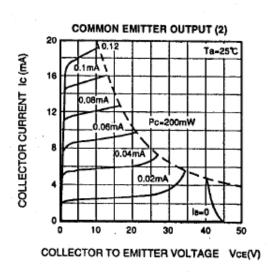
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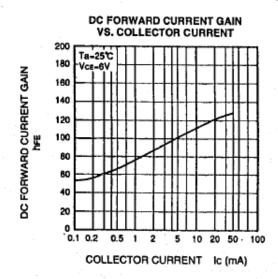
#### TYPICAL CHARACTERISTICS

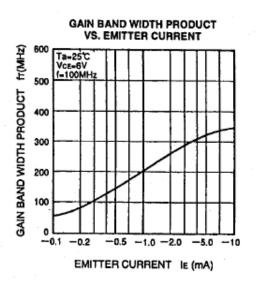












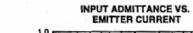
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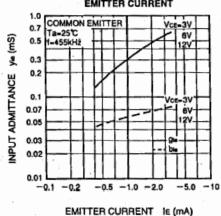
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## COMMON EMITTER, y PARAMETER (TYPICAL VALUE)

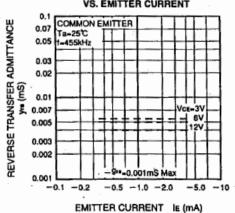
| y Parameter |       | f=455kHz<br>VcE=6V<br>IE= - 1mA | SV VCE=6V VCE=6V |          | f=100MHz<br>Vce≖6V<br>le=−1mA |
|-------------|-------|---------------------------------|------------------|----------|-------------------------------|
| yle         | gie   | 0.30                            | 0.30             | 0.38     | 4.4                           |
| (mS)        | bie   | 0.06                            | 0.12             | 1.40     | 11.0                          |
| . Yre       | - gre | 0.001Max                        | 0.001Max         | 0.005Max | 0.05Max                       |
| (mS)        | bre   | 0.005                           | 0.010            | 0.11     | 1.0                           |
| yle         | gte . | 50                              | 46               | 37       | 25 ,                          |
| (mS)        | - bie | 1.0Max                          | 1.0Max           | 2.8      | 16                            |
| You         | goe   | 0.010                           | 0.012            | 0.03     | 0.32                          |
| (mS)        | boe   | 0.011                           | 0.022            | 0.18     | 1.3                           |

## **COMMON EMITTER, 455kHz y PARAMETER**

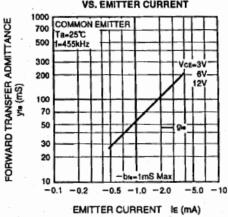




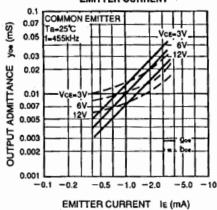
REVERSE TRANSFER ADMITTANCE VS. EMITTER CURRENT



## FORWARD TRANSFER ADMITTANCE VS. EMITTER CURRENT

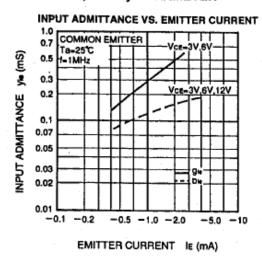


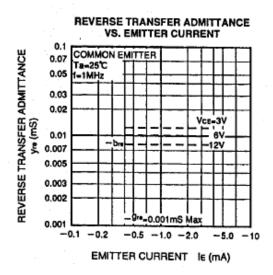
#### OUTPUT ADMITTANCE VS. EMITTER CURRENT

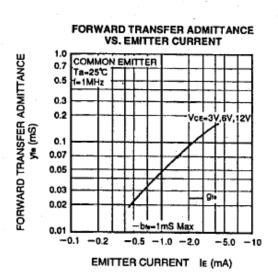


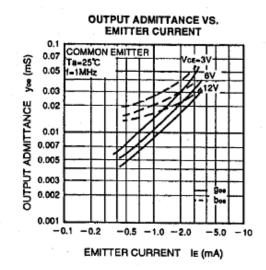
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# COMMON EMITTER, 1MHz y PARAMETER

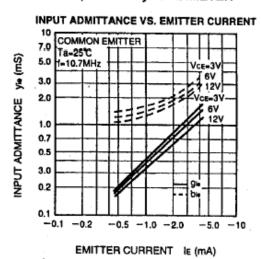


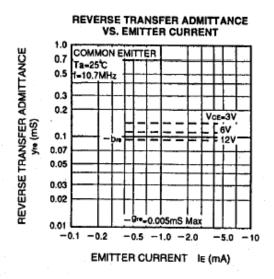






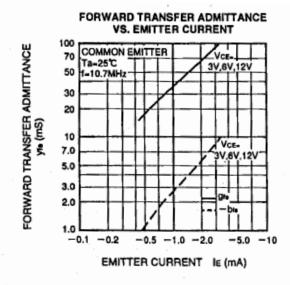
# COMMON EMITTER, 10.7MHz y PARAMETER

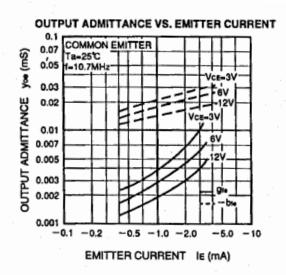




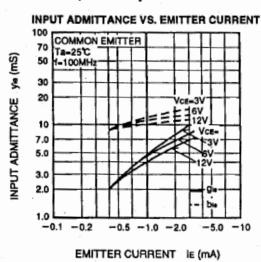
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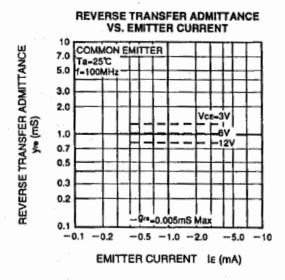
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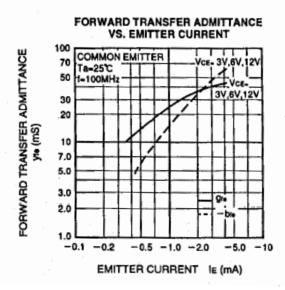


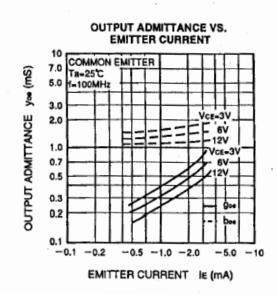


## COMMON EMITTER, 100MHz y PARAMETER











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